Docket No. 5000-5291

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Takefumi NISHIMUTA; Hiroshi MIYAGI; Tadahiro OHMI; Shigetoshi SUGAWA; and Akinobu Applicant(s): **TERAMOTO** Serial No.: **TBA** Group Art Unit: **TBA** Filed: Herewith Examiner: **TBA** For: MIS TRANSISTOR AND CMOS TRANSISTOR Customer No.: 27123 INFORMATION DISCLOSURE STATEMENT Mail Stop Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450 Sir: Pursuant to Rule 56, applicant hereby calls the attention of the Patent Office to the references listed on the attached Form PTO 1449. Copy(ies) of these references 🛛 are attached 🗌 were filed in related application U.S. Serial No(s) _____, filed _____, respectively. This document is being filed within three (3) months of the filing date of the application П Please charge the \$180 fee to Deposit Account No. 13-4500, Order No. _ This document is being concurrently filed with the above-identified application \bowtie This document is being concurrently filed with an Request for Continued Examination (RCE) \Box This document is being filed prior to a first Office Action This document is accompanied by a Search Report/Communication cited in a corresponding PCT or \boxtimes foreign counterpart application. X The Commissioner is hereby authorized to charge any additional fees which may be required for this Information Disclosure Statement, or credit any overpayment to Deposit Account No. 13-4500, Order No. 5000-5291. A DUPLICATE COPY OF THIS SHEET IS ATTACHED. Respectfully submitted, MORGAN, & FINNEGAN, L.L.P. Dated: December 13, 2005 Steven F. Meyer Registration No. 35,613 Correspondence Address:

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10/560706 IAP9 Rec'd PCT/PTO 13 DEC 2009

INFORMATION DISCLOSURE CITATION			Attorney Docket No. 5000-5291 Serial No.: To Be Assigned Applicants: Takefumi NISHIMUTA; Hiroshi MIYAGI; Tadahiro OHMI; Shigetoshi SUGAWA; and Akinobu TERAMOTO					
							p Art Unit: Assigned	
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Examiner Initial	Patent Number	Publication Date		Name	Class		Sub- Class	Filing Date
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	 Y. Choi et al, "FinFET Process Refinements for Improved Mobility and Gate Work Function Engineering", Electron Devices Meeting, IEDM 02 Digest, pps 259-262, December 2002 Y. Choi et al, "Nanoscale CMOS Spacer FinFET for the Terabit Era", IEEE Electron Device Letters, Vol 23, No. 1, 							
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